

FDPF44N25TRDTU

FDPF44N25TRDTU Information



For Reference Only

Part Number FDPF44N25TRDTU

Manufacturer Fairchild/ON Semiconductor

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Perceptation MOSFET N. CH 250V 44A TO 220E

DescriptionMOSFET N-CH 250V 44A TO-220F**Package**TO-220-3 Full Pack, Formed Leads

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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FDPF44N25TRDTU Specifications

Manufacturer Part NumberFDPF44N25TRDTUManufacturerFairchild/ON SemiconductorCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-220-3 Full Pack, Formed LeadsSeriesUniFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)250VCurrent - Continuous Drain (Id) @ 25°C44A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs61nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2870pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)38W (Tc)Rds On (Max) @ Id, Vgs69 mOhm @ 22A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220F (LG-Formed)		
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SeriesUniFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)250VCurrent - Continuous Drain (Id) @ 25°C44A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs61nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2870pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)38W (Tc)Rds On (Max) @ Id, Vgs69 mOhm @ 22A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220F (LG-Formed)		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)250VCurrent - Continuous Drain (Id) @ 25°C44A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs61nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2870pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)38W (Tc)Rds On (Max) @ Id, Vgs69 mOhm @ 22A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220F (LG-Formed)	Package	TO-220-3 Full Pack, Formed Leads
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)250VCurrent - Continuous Drain (Id) @ 25°C44A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs61nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2870pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)38W (Tc)Rds On (Max) @ Id, Vgs69 mOhm @ 22A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220F (LG-Formed)	Series	UniFET?
Drain to Source Voltage (Vdss)250VCurrent - Continuous Drain (Id) @ 25°C44A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs61nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2870pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)38W (Tc)Rds On (Max) @ Id, Vgs69 mOhm @ 22A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220F (LG-Formed)	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C 44A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 61nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2870pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 38W (Tc) Rds On (Max) @ Id, Vgs 69 mOhm @ 22A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220F (LG-Formed)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs61nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2870pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)38W (Tc)Rds On (Max) @ Id, Vgs69 mOhm @ 22A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220F (LG-Formed)	Drain to Source Voltage (Vdss)	250V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package 5V @ 250μA 61nC @ 10V 2870pF @ 25V Through Hole	Current - Continuous Drain (Id) @ 25°C	44A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 2870pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 69 mOhm @ 22A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package 61nC @ 10V 2870pF @ 25V 2870	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Through Hole Supplier Device Package 2870pF @ 25V 2870pF @ 25	Vgs(th) (Max) @ Id	5V @ 250μA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)38W (Tc)Rds On (Max) @ Id, Vgs69 mOhm @ 22A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220F (LG-Formed)	Gate Charge (Qg) (Max) @ Vgs	61nC @ 10V
FET Feature - Power Dissipation (Max) 38W (Tc) Rds On (Max) @ Id, Vgs 69 mOhm @ 22A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220F (LG-Formed)	Input Capacitance (Ciss) (Max) @ Vds	2870pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 69 mOhm @ 22A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220F (LG-Formed)	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs69 mOhm @ 22A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220F (LG-Formed)	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220F (LG-Formed)	Power Dissipation (Max)	38W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220F (LG-Formed)	Rds On (Max) @ Id, Vgs	69 mOhm @ 22A, 10V
Supplier Device Package TO-220F (LG-Formed)	Operating Temperature	-55°C ~ 150°C (TJ)
••	Mounting Type	Through Hole
TO 200 0 F H P 1 F 1 H	Supplier Device Package	TO-220F (LG-Formed)
Package / Case TO-220-3 Full Pack, Formed Leads	Package / Case	TO-220-3 Full Pack, Formed Leads
Report errors?		Report errors?

FDPF44N25TRDTU Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

FDPF44N25TRDTU Payment Methods

































If you have any question about FDPF44N25TRDTU, please do not hesitate to contact us!

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